Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	883	(judg$5 adj3 cell) and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:26
S2	234	((judgement judgment) adj3 cell) and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:23
S3	1895	365/145.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:24
S4	1	S3 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:24
S5	4	S2 and (S3 or ferroelectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:25
S6	5	((judgement judgment) adj3 cell) and (365/145.ccls. or ferroelectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:26
S7	1898	365/145.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:27
S8	423	S7 and ((1T/1C) (one adj3 transistor adj3 one adj3 capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:34

S9	1148	365/210.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:27
S10	3787	365/200.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:27
S11	3281	365/201.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:29
S12	1247	(S7 or ferroelectric) and ((reference dummy) adj3 cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:31
S13	1	S7 and S9 and S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:30
S14	1267	(S7 or ferroelectric or FeRAM) and ((reference dummy) adj3 cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:31
S15	5	S14 and S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:32
S16	1479	365/207.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:32

S17	0	S15 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:33
S18	1088	(S7 or ferroelectric or FeRAM) and ((1T/1C) (one adj3 transistor adj3 one adj3 capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:35
S19	0	S18 and S10 and S11 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:34
S21	47	S18 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:34
S22	24	S18 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:34
S23	53	S18 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:34
S24	364	S14 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:35
S25	245	S24 and (plate adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:35

S26	1	S25 and S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:35
S27	1898	365/145.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:13
S28	1088	(S27 or ferroelectric or FeRAM) and ((1T/1C) (one adj3 transistor adj3 one adj3 capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:13
S29	1267	(S27 or ferroelectric or FeRAM) and ((reference dummy) adj3 cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:13
S30	364	S29 and S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:14
S31	317	S30 and (reference dummy) with ((2T/2C) (2C/2T) or (two near5 transistor near3 two capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:15
S32	276	S30 and ((reference dummy) near3 cell) with ((2T/2C) (2C/2T) or (two near5 transistor near3 two capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:23
S33	234	((judgement judgment) adj3 cell) and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:15

S34	0	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:15
S35	3787	365/200.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:16
S36	3281	365/201.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:16
S37	1	S32 and S35 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:16
S38	17	S32 and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:20
S39	8	S32 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:21
S40	24	S32 and (S36 S35)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:21
S41	2218	((reference dummy) near3 cell) with ((2T/2C) (2C/2T) or (two near5 transistor near3 two capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:23

S42	113	S41 and (S35 S36)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:23
S43	1899	365/145.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:47
S44	1480	365/207.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/10/06 12:47
S45	1090	(S43 or ferroelectric or FeRAM) and ((1T/1C) (one adj3 transistor adj3 one adj3 capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:47
S46	20	S45 and S44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:47
S47	7	(US-20040017704-$).did. or (US-6721200-$ or US-6560137-$ or US-5751628-$ or US-6501674-$ or US-6363002-$ or US-6078529-$).did.	US-PGPUB; USPAT	OR	ON	2005/10/06 13:04
S48	7	S47 and (dummy reference) adj3 cell	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 13:04